

AMENDMENTS TO THE CLAIMS

1. (Currently amended) A well structure in a high voltage device, comprising;
a first well formed in a substrate, the first well having an implant of an opposite conductive type from the substrate;
a second well isolated from the first well, the second well having an implant of the same conductive type as the substrate;
a field stop implant region formed between the first well and the second well and spaced apart from each of the first well and the second well by a given distance, the field stop implant region having an implant of the same conductive type as the substrate; and
a pick-up region ~~overlapped on~~ disposed above the field stop implant region, the pick-up region having an implant of the same conductive type as the field stop implant region.
2. (Original) The well structure as claimed in claim 1, wherein the substrate is a P type substrate.
3. (Currently amended) The well structure as claimed in claim 1, wherein the first well is an N-well into which phosphorus (P) ~~phosphorous (Ph)~~ is implanted.
4. (Original) The well structure as claimed in claim 1, wherein the second well is a P-well into which boron (B) is implanted.
5. (Original) The well structure as claimed in claim 1, wherein the field stop implant region is formed by implanting boron (B).
6. (Original) The well structure as claimed in claim 1, wherein the spaced distance between the first well and the field stop implant region is in the range of 0.5 μm to 1.5 μm .
7. (Original) The well structure as claimed in claim 1, wherein the spaced distance between the second well and the field stop implant region is 0.5 μm to 1.5 μm .

8. (Original) The well structure as claimed in claim 1, wherein the pick-up region is formed by implanting boron (B) with high concentration.